

Shanghai Senchip Microelectronics Co., Ltd

Transient Voltage Suppressor

SCLAMP0521P

Features

- Peak Power Dissipation 20W(8×20us Waveform)
- Stand-off Voltage:5.0V
- Low capacitance(<0.5pF)for high-speed interfaces
- No insertion loss to 2.0GHz
- Replacement for MLV(0402)
- Protects I/O Port
- Low Clamping Voltage
- Low Capacitance
- Meets MSL 1 Requirements
- ROHS compliant

IEC COMPATIBILITY (EN61000-4)

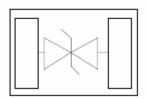
- IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)

Main applications

- High Speed Line:USB1.0/2.0,VGA,DVI,SDI
- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- Peripherals



DFN1006





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Maximum rating(Tamb=25[°]C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20µs waveform)	Pppp	20	Watts
ESD Rating per IEC61000-4-2: Contact		8	101
Air		15	KV
Lead Soldering Temperature	TL	260 (10 sec.)	°C
Operating Temperature Range	ΤJ	-55 ~ 150	°C
Storage Temperature Range	Тѕтс	-55 ~ 150	°C
Lead Solder Temperature - Maximum (10 Second Duration)	TL	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit

values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not

implied,damage may occur and reliability may be affected.

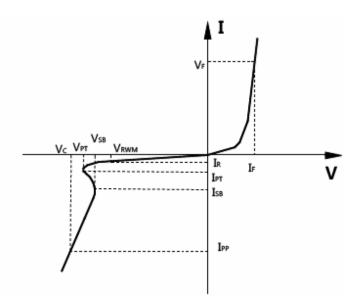
Electrical characteristics(Tamb=25℃ Unless Otherwise Specified)

	V 1.00	I _R @ V _{RWM}	V _{PT} @ 1 mA		Vc	Capacitance	
Device	ice V _{RWM}		(Volts)		@1A	@ V _R = 0 V, 1 MHz (pF)	
	(V)	(uA)	Min	Max	(V)	Тур	Max
SCLAMP0521P	5.0	1	6.0	10	15.0	0.3	0.5

Junction capacitance is measured in VR=0V,F=1MHz

Electrical Parameters (T=25℃)

Symbol	Parameter	
Vrwm	Working Peak Reverse Voltage	
VPT	Punch-Through Voltage@ IPT	
Vsa	Snap-Back Voltage@ I _{SB}	
Vc	Clamping Voltage @ IPP	
Ιτ	Test Current	
IRM	Leakage current at VRWM	
IPP	Peak pulse current	
Co	Off-state Capacitance	
CJ	Junction Capacitance	



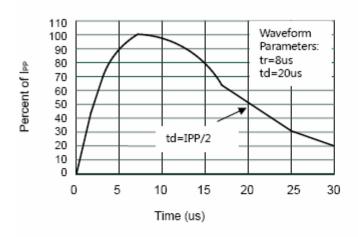
^{*}Other voltages may be available upon request.

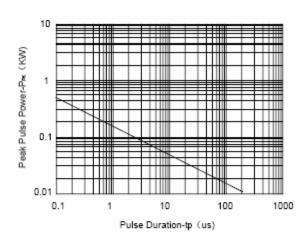
^{1.} Nonrepetitive current pulse, per Figure 1.



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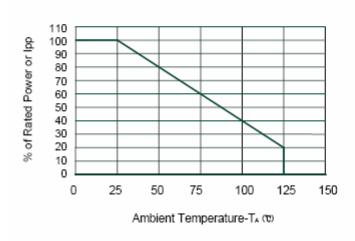
Typical Characteristics

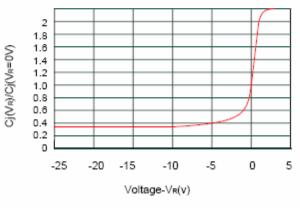




Pulse Waveform

Non-Repetitive Peak Pulse Power vs. Pulse Time





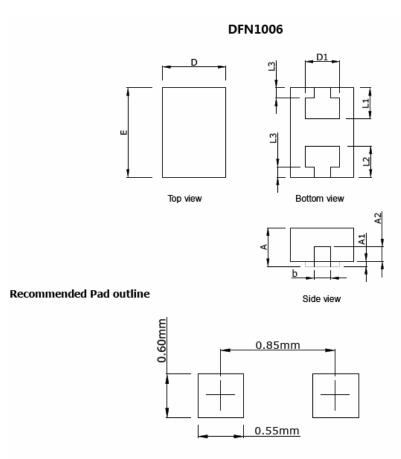
Power Derating Curve

Junction Capacitance vs. Reverse Voltage



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Outline Drawing - DFN1006



Completel	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.40	0.50	0.016	0.020	
A1		0.05		0.002	
A3	0.15REF		0.006REF		
D	0.55	0.65	0.022	0.026	
Е	0.95	1.05	0.037	0.041	
D1	0.25	0.35	0.010	0.014	
b	0.15	0.25	0.006	0.001	
L1	0.25	0.45	0.010	0.018	
L2	0.23	0.43	0.009	0.017	
L3	0.10REF		0.00	4REF	

Ordering Information

Device	Qty per Reel	Reel Size
SCLAMP0521P	5000	7 Inch